

Silicon PNP Power Transistors

2SB1063

DESCRIPTION

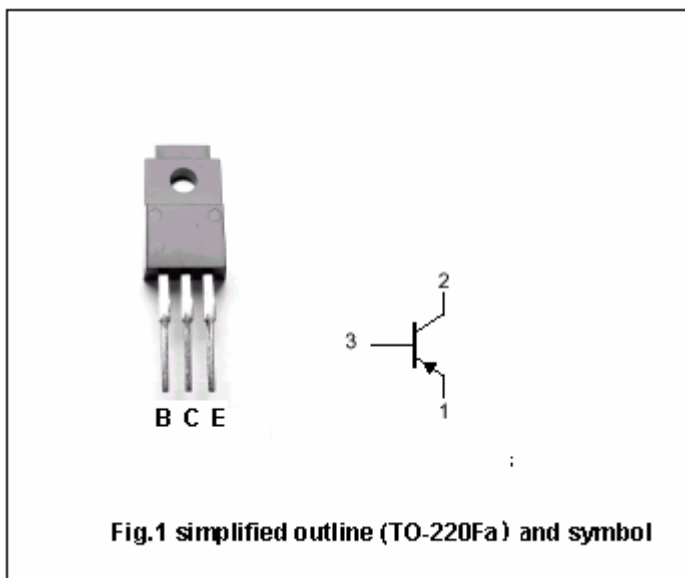
- With TO-220Fa package
- Complement to type 2SD1499
- Wide area of safe operation
- High  $f_T$

APPLICATIONS

- For high power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-100	V
$V_{CEO}$	Collector -emitter voltage	Open base	-100	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-5	A
$I_{CM}$	Collector current-peak		-8	A
$P_C$	Collector power dissipation	$T_a=25$	2.0	W
		$T_C=25$	40	
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-3A ; I <sub>B</sub> =-0.3A			-2.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-5V			-1.8	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-100V; I <sub>E</sub> =0			-50	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-3V; I <sub>C</sub> =0			-50	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-20mA ; V <sub>CE</sub> =-5V	20			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	40		200	
h <sub>FE-3</sub>	DC current gain	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-5V	20			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-5V		20		MHz
C <sub>OB</sub>	Collector output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V; f=1MHz		170		pF

◆ h<sub>FE-2</sub> Classifications

R	Q	P
40-80	60-120	100-200

PACKAGE OUTLINE

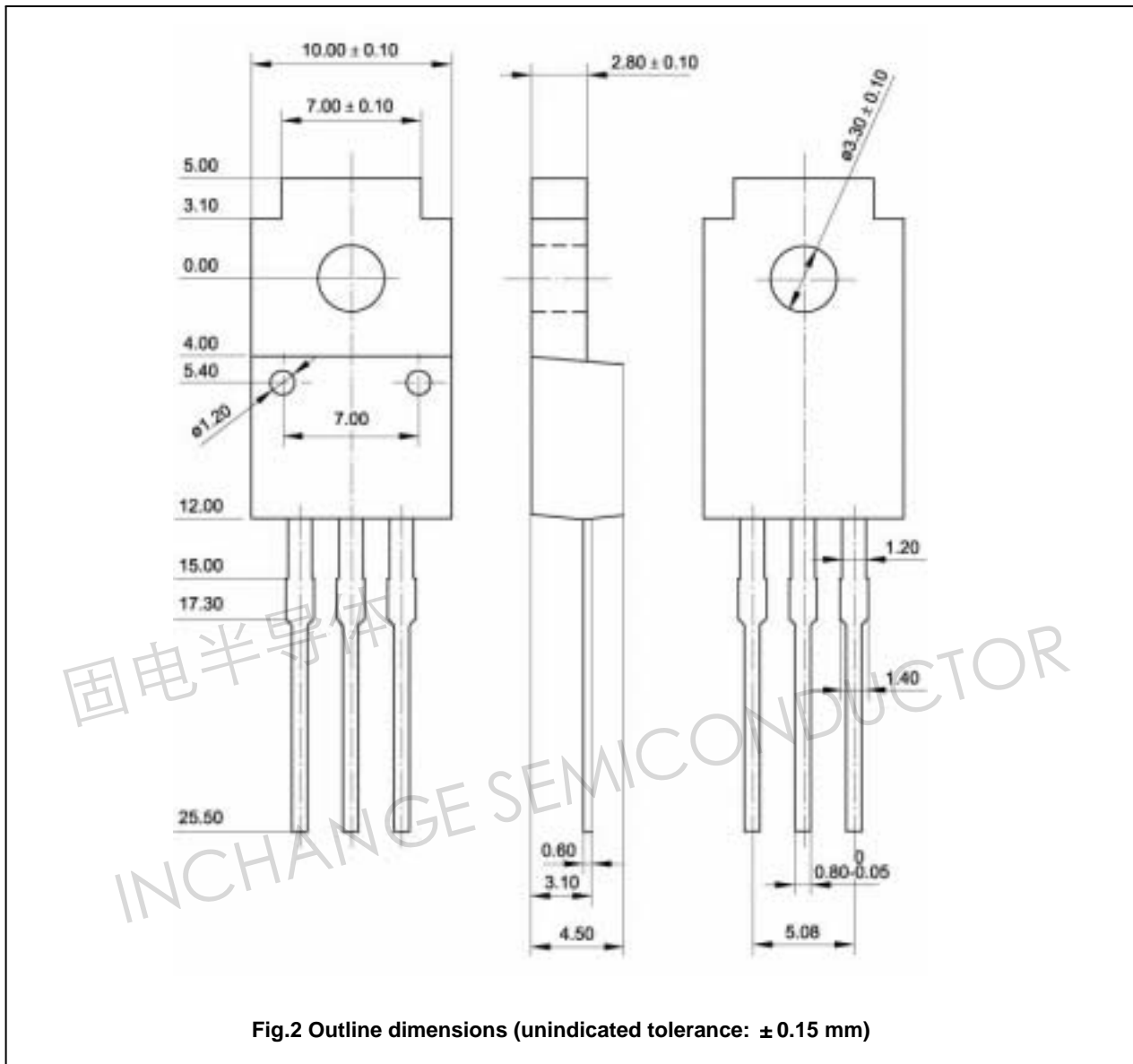


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.15$  mm)